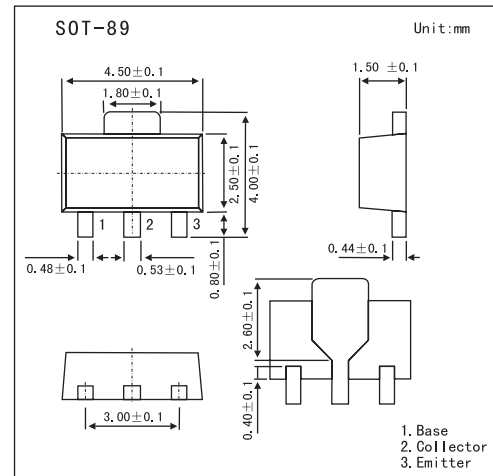


Silicon PNP Epitaxial Planar Type

2SB766,2SB766A

■ Features

- Large collector power dissipation PC
- Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit	
Collector-base voltage	2SB766 2SB766A	V_{CB0}	-30	V
			-60	
Collector-emitter voltage	2SB766 2SB766A	V_{CE0}	-25	V
			-50	
Emitter-base voltage	V_{EBO}	-5	V	
Collector current	I_C	-1	A	
Peak collector current	I_{CP}	-1.5	A	
Collector power dissipation	P_C	-1	W	
Junction temperature	T_j	150	$^\circ\text{C}$	
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$	

2SB766,2SB766A

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base voltage	2SB766	Ic = -10 μ A, IE = 0	-30			V
	2SB766A		-60			
Collector-emitter voltage	2SB766	Ic = -2 mA, IB = 0	-25			V
	2SB766A		-50			
Emitter-base voltage	VEBO	IE = -10 μ A, Ic = 0	-5			V
Collector-base cutoff current	ICBO	V _{CB} = -20 V, IE = 0			-0.1	nA
Forward current transfer ratio	hFE	V _{CE} = -10 V, Ic = -500 mA	85		340	
		V _{CE} = -5 V, Ic = -1 A	50			
Collector-emitter saturation voltage	V _{CE(sat)}	Ic = -500 mA, IB = -50 mA		-0.2	-0.4	V
Base-emitter saturation voltage	V _{BE(sat)}	Ic = -500 mA, IB = -50 mA		-0.85	-1.2	V
Transition frequency	f _T	V _{CB} = -10 V, IE = 50 mA, f = 200 MHz		200		MHz
Collector output capacitance	C _{ob}	V _{CB} = -10 V, IE = 0, f = 1 MHz		20	30	pF

■ hFE Classification

Marking	2SB766(A)/2SB766A(B)		
Rank	Q	R	S
hFE	85~170	120~240	17~340